

### Description

The HSS2310A is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

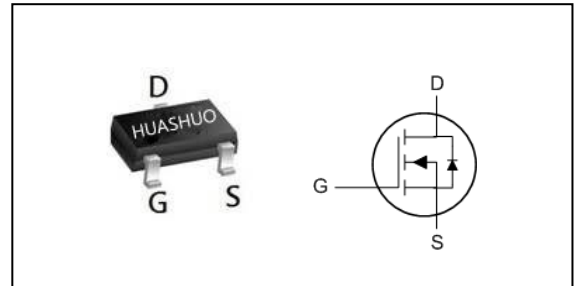
The HSS2310A meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

### Product Summary

$V_{DS}$	60	V
$R_{DS(ON),typ}$	80	m $\Omega$
$I_D$	2.3	A

### SOT23 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V_1$	2.3	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V_1$	1.8	A
$I_{DM}$	Pulsed Drain Current <sub>2</sub>	9.2	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sub>3</sub>	1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sub>1</sub>	---	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sub>1</sub>	---	80	$^\circ\text{C/W}$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.054	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sub>2</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	---	80	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	---	85	110	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.96	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	---	13	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	5	7.0	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.68	2.4	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.9	2.7	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =2A	---	1.6	3.2	ns
T <sub>r</sub>	Rise Time		---	7.2	13	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	50	
T <sub>f</sub>	Fall Time		---	14.4	28.8	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	511	715	pF
C <sub>oss</sub>	Output Capacitance		---	38	53	
C <sub>riss</sub>	Reverse Transfer Capacitance		---	25	35	

**Diode Characteristics**

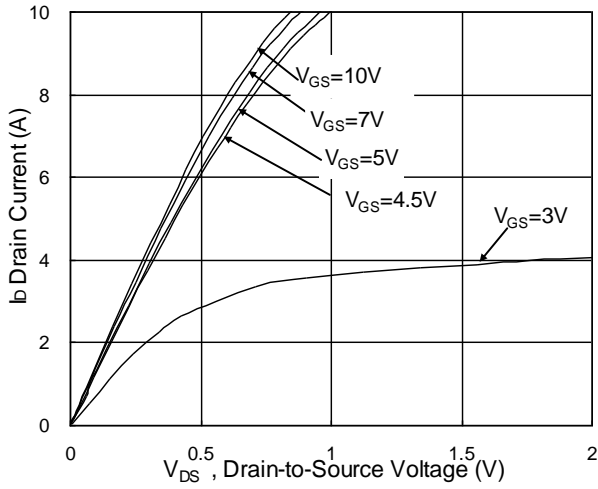
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sub>1,4</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	2.3	A
I <sub>SM</sub>	Pulsed Source Current <sub>2,4</sub>		---	---	9.2	A
V <sub>SD</sub>	Diode Forward Voltage <sub>2</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =2A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	9.7	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	5.8	---	nC

Note :

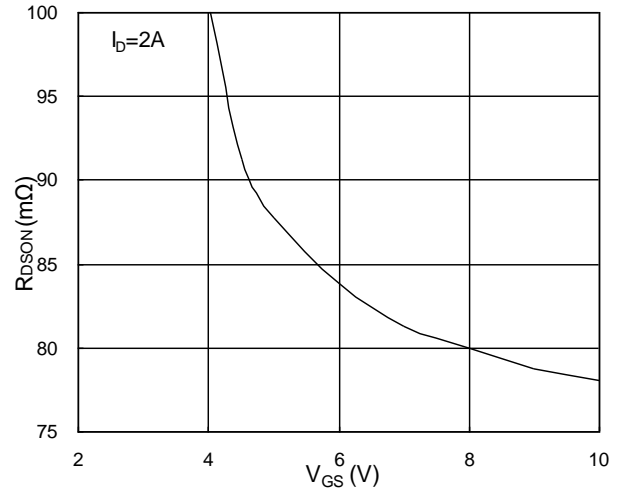
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



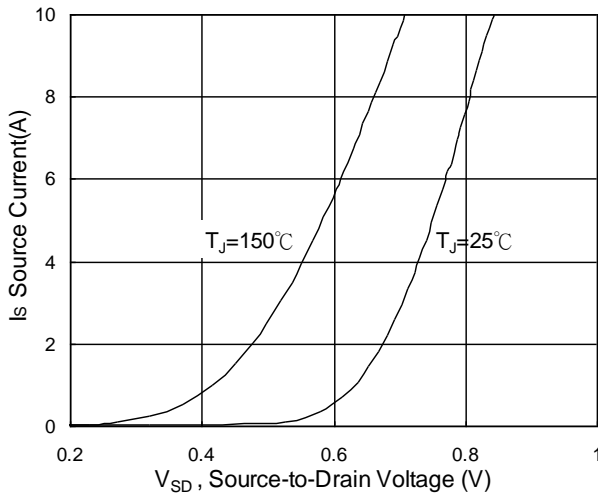
### Typical Characteristics



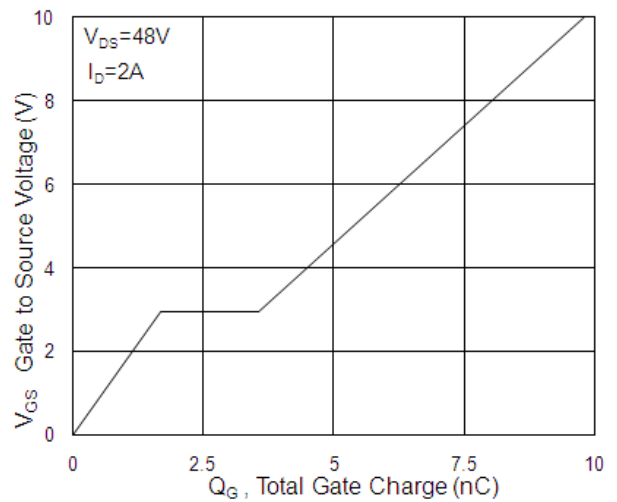
**Fig.1 Typical Output Characteristics**



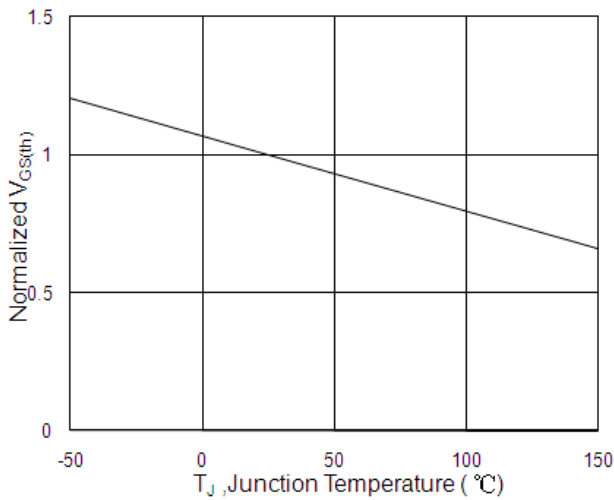
**Fig.2 On-Resistance v.s Gate-Source**



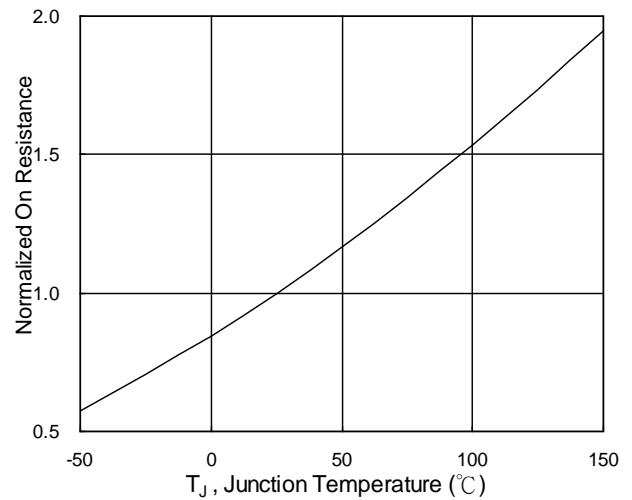
**Fig.3 Forward Characteristics of Reverse**



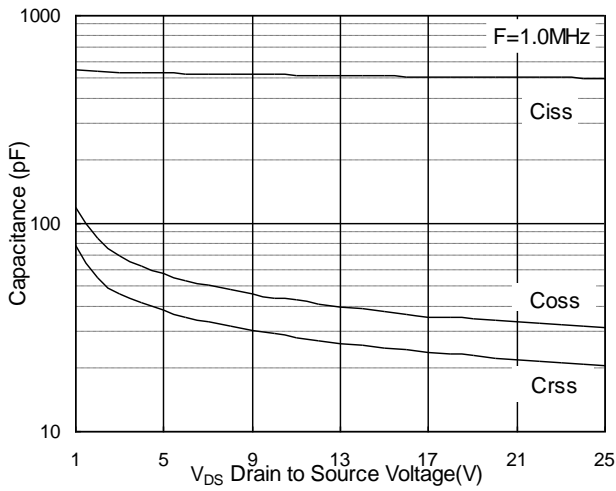
**Fig.4 Gate-Charge Characteristics**



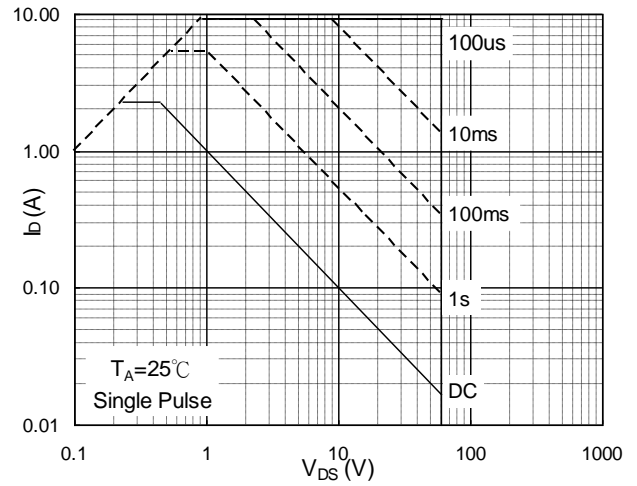
**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



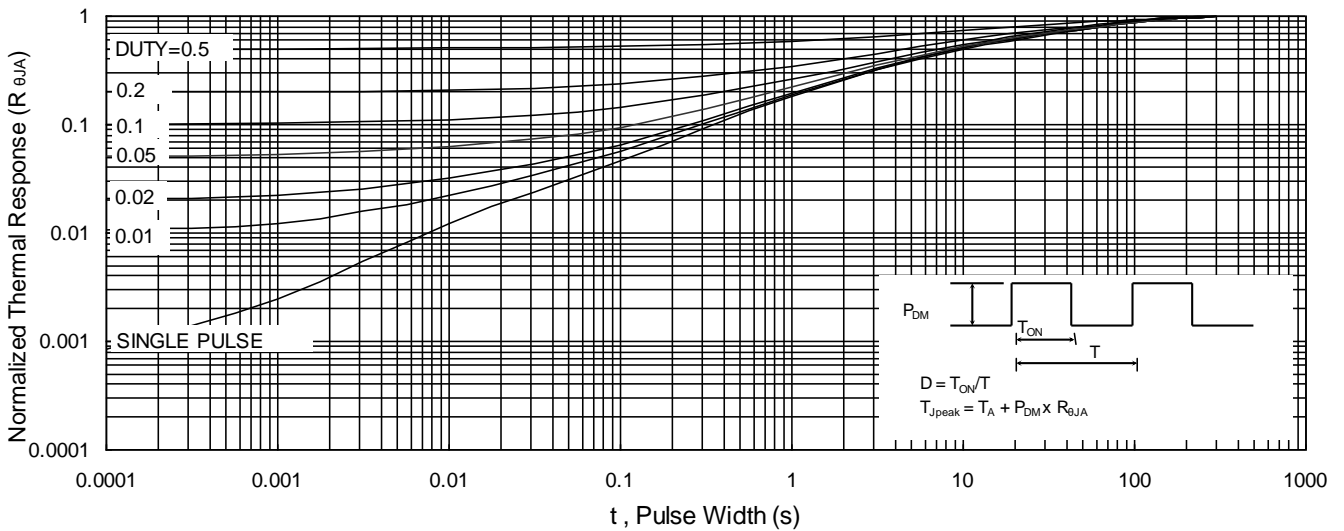
**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**



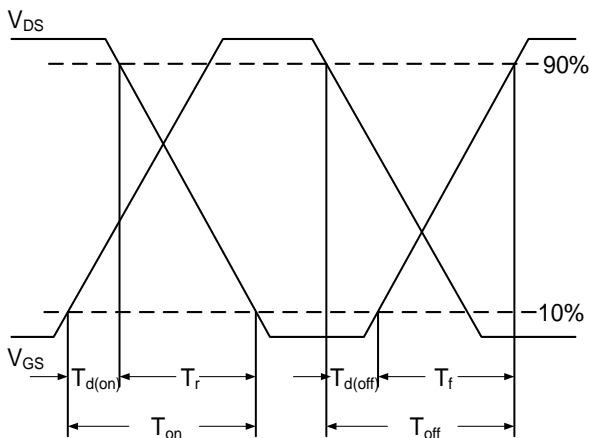
**Fig.7 Capacitance**



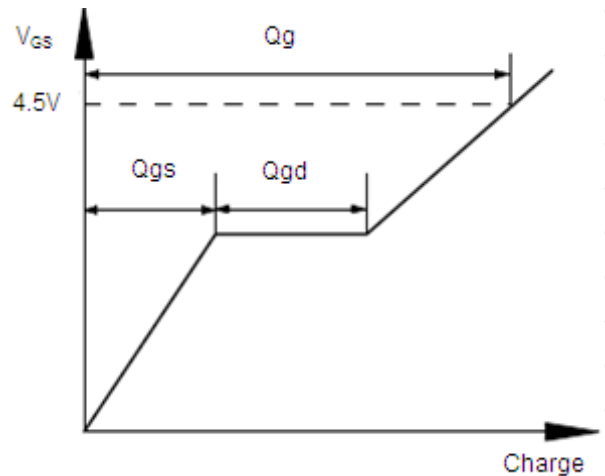
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**

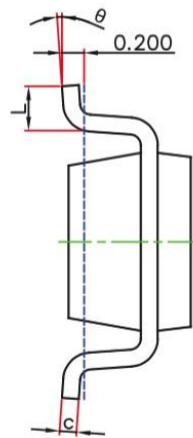
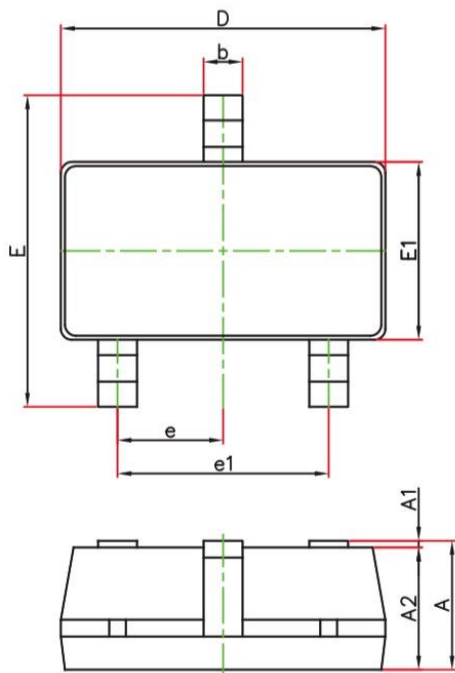


**Fig.11 Gate Charge Waveform**



## Ordering Information

Part Number	Package code	Packaging
HSS2310A	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°